

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant(s): Paul D. Agnello, et al.

Examiner: Unassigned

Serial No: Unassigned

Art Unit: Unassigned

Filed: Herewith

Docket: YOR91990281US3 (12795AB)

For: METHOD AND STRUCTURE FOR  
CONTROLLING THE INTERFACE  
ROUGHNESS OF COBALT DISILICIDE

Dated: October 22, 2003

Commissioner for Patents  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Sir:

In accordance with 37 C.F.R §§1.97 and 1.98, it is requested that the following references, which are also listed on the attached Form PTO-1449, be made of record in the above-identified case.

1. U.S. Patent No. 5,510,295, issued April 23, 1996, to Cabral, Jr. et al.;

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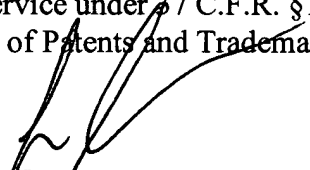
**CERTIFICATE OF MAILING BY EXPRESS MAIL**

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I hereby certify that this correspondence is being deposited with the United States Postal Service Express Mail Post Office to Addressee service under 37 C.F.R. §1.10 on the date indicated above and is addressed to the Commissioner of Patents and Trademarks, Alexandria, VA 22313-1450.

Dated: October 22, 2003

  
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Leslie S. Szivos, Ph.D.

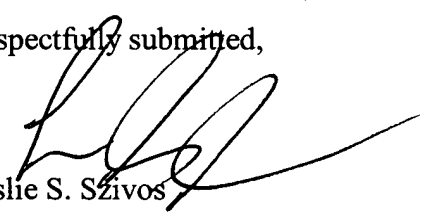
2. U.S. Patent No. 5,608,226, issued March 4, 1997 to Yamada et al.;
3. U.S. Patent No. 5,624,869, issued March 4, 1997 to Yamada, et al.;
4. U.S. Patent No. 5,624,869, issued April 29, 1997 to Agnello, et al.;
5. U.S. Patent No. 5,828,131, issued October 27, 1998 to Cabral, Jr., et al.;
5. M. Lawrence, et al.,(1991),"Growth of Epitaxial CoSi<sub>2</sub> on (100)Si," Appl. Phys. Lett., Vol. 58, No. 12, pp. 1308-1310; and
6. C. Cabral, Jr., et al.,(1995),"In-Situ X Ray Diffractin and Resistivity Analysis of CoSi<sub>2</sub> Phase Formation With and Without a Ti Interlayer at Rapid Thermal Annealing Rates," Mat. Res. Sco. Symp. Proc., Vol. 375, pp. 253-258.

Pursuant to 37 C.F.R. §1.98(d), copies of the above-listed references are not provided, as they were all previously submitted to the Examiner in connection with the parent case, Serial No. 09/416,083, filed on October 12, 1999.

Consideration of this Information Disclosure Statement is respectfully requested.

Inasmuch as this Information Disclosure Statement is being submitted in accordance with the schedule set out in 37 C.F.R. § 1.97(b), no statement or fee is required.

Respectfully submitted,



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<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>	Docket Number (Optional) <b>YOR919990281US3 (12795AB)</b>	Application Number <b>Unassigned</b>
	Applicant(s) <b>Paul D. Agnello, et al.</b>	
	Filing Date <b>Herewith</b>	Group Art Unit <b>Unassigned</b>

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,510,295	4/23/96	Cabral, Jr., et al.			
		5,608,226	3/4/97	Yamada, et al.			
		5,624,869	4/29/97	Agnello, et al.			
		5,828,131	10/27/98	Cabral, Jr., et al.			

**FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		M. Lawrence, et al.,(1991),"Growth of Epitaxial CoSi2 on (100)Si," Appl. Phys. Lett., Vol. 58, No. 12, pp. 1308-1310
		C. Cabral, Jr., et al.,(1995),"In-Situ X Ray Diffractin and Resistivity Analysis of CoSi2 Phase Formation With and Without a Ti Interlayer at Rapid Thermal Annealing Rates," Mat. Res. Sco. Symp. Proc., Vol. 375, pp. 253-258.

EXAMINER	DATE CONSIDERED
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**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.